



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(on)} max	I _D max T _C = +25°C		
201/	$15m\Omega @ V_{GS} = -10V$	-52.7 A		
-30V	$25m\Omega$ @ $V_{GS} = -5V$	-40.8 A		

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile—Ideal for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

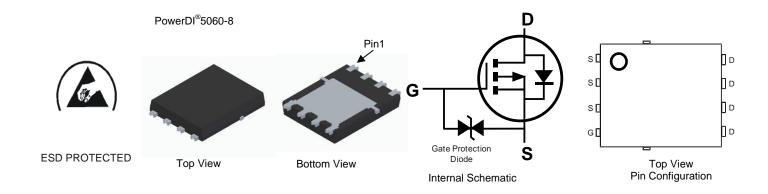
Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC converters
- Power management functions
- Analog switches

Mechanical Data

- Package: PowerDI[®]5060-8 (Type UX)
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Number	rackaye	Qty.	Carrier	
DMP3021SPSW-13	PowerDI5060-8 (Type UX)	2,500	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



) | |= Manufacturer's Marking P3021SW = Product Type Marking Code YY = Date Code Marking YY = Last Digit of Year (ex: 22 = 2022) WW = Week Code (01 to 53)

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-30	V		
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	-10.6 -8.5	А
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	-52.7 -42.2	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	-3.2	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-197	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-197	Α
Avalanche Current (Note 8) L = 1mH			I _{AS}	-14.5	А
Avalanche Energy (Note 8) L = 1mH			Eas	104	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.8	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		R _{θJA}	69.5	°C/W
Total Power Dissipation (Note 6) T _A = +25°C		P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	49.6	°C/W
Thermal Resistance, Junction to Case (Note 7)	R _{0JC}	2	°C/W	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad). 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.



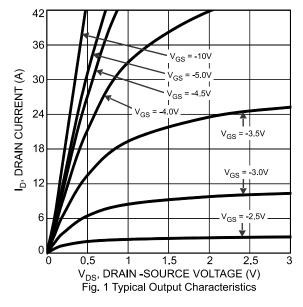
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

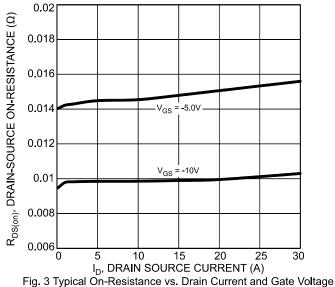
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μA	V _{DS} = -30V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	_	-2.5	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	D	_	9.8	15	m0	V _{GS} = -10V, I _D = -8A	
Static Dialii-Source Oil-Resistance	R _{DS(on)}	_	14.3	25	mΩ	$V_{GS} = -5V, I_D = -5A$	
Diode Forward Voltage	V _{SD}	_	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1799	_	pF	V _{DS} = -15V, V _{GS} = 0V, - f = 1.0MHz	
Output Capacitance	Coss	_	259	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	225	_	pF		
Gate Resistance	R_g	_	2.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -5V)	Qg	_	17.4	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	34	_	nC	\	
Gate-Source Charge	Q _{gs}	_	5.1	_	nC	$V_{DS} = -15V, I_{D} = -10A$	
Gate-Drain Charge	Q _{gd}	_	8.4	_	nC	1	
Turn-On Delay Time	t _{D(on)}	_	6.5	_	ns		
Turn-On Rise Time	t _R	_	18.3	_	ns	$V_{DD} = -15V$, $V_{GS} = -10V$, $R_G = 3\Omega$, $I_D = -10A$	
Turn-Off Delay Time	t _{D(off)}	_	35.8	_	ns		
Turn-Off Fall Time	t _F	_	23.7	_	ns]	
Reverse Recovery Time	t _{RR}	_	14.9	_	ns	L 0A 41/44 500A/v-	
Reverse Recovery Charge	Q _{RR}	_	15	_	nC	$I_S = -8A$, $dI/dt = 500A/\mu s$	

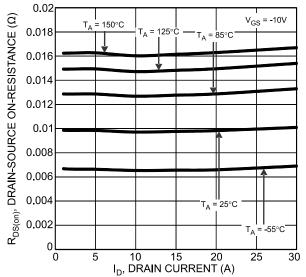
Notes:

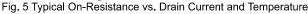
^{9.} Short duration pulse test used to minimize self-heating effect.10. Guaranteed by design. Not subject to product testing.

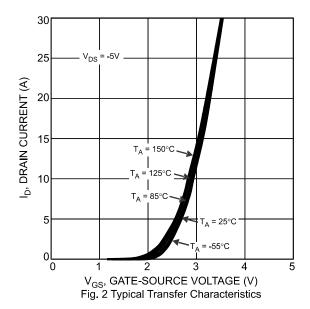












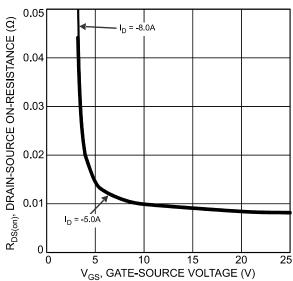


Fig. 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

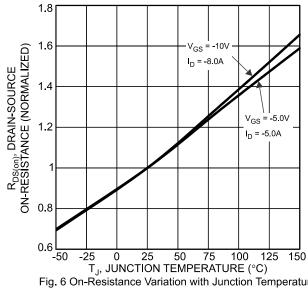
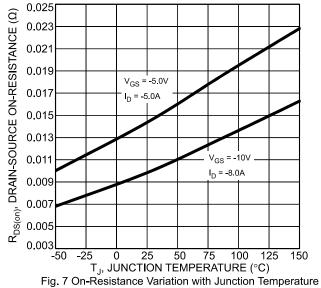
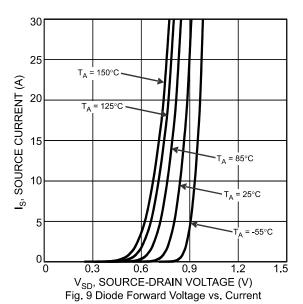
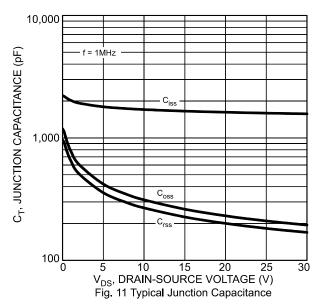


Fig. 6 On-Resistance Variation with Junction Temperature









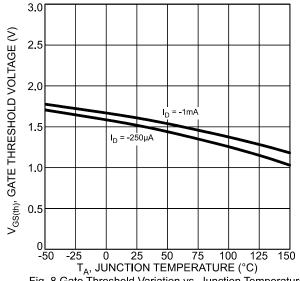
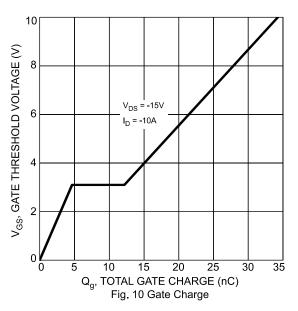
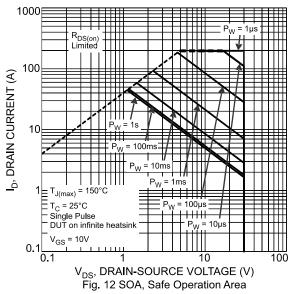


Fig. 8 Gate Threshold Variation vs. Junction Temperature







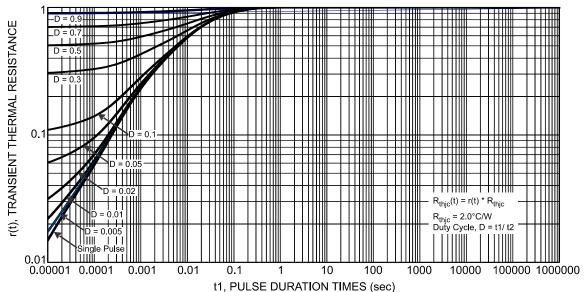


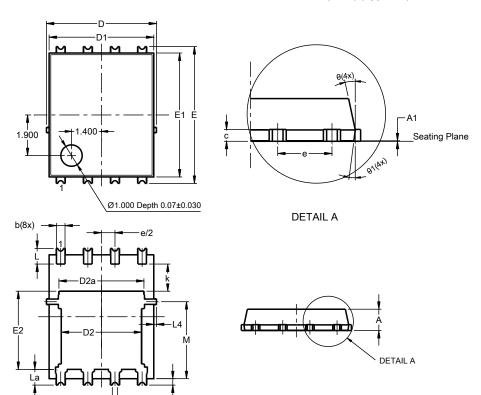
Fig. 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type UX)

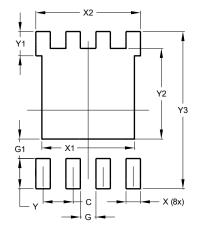


PowerDI5060-8 (SWP)					
(Type UX)					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0	0.05	-		
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	().25REF	•		
С	0.230	0.330	0.277		
D	5	.15 BS0)		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a			3.98		
Е	6	.40 BS0			
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е	1.27BSC				
k	1.05		-		
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
M	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

Suggest Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value			
Dilliensions	(in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	4.420			
Υ	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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